
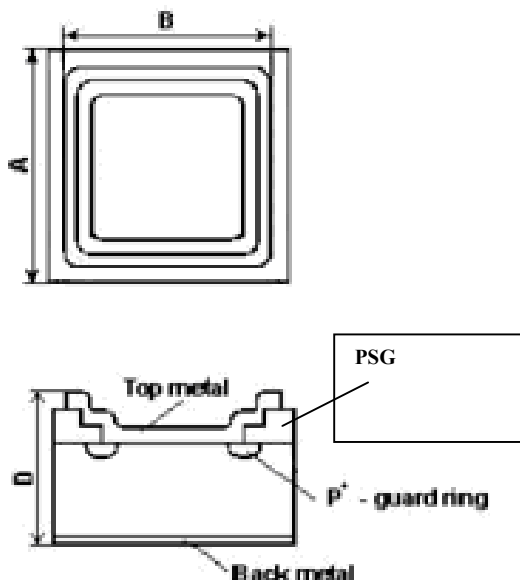


SCHOTTKY DIODES. KDS- 01030D.

PRELIMINARY.

Sep.2011

 VSP-MIKRON	1A/30V. Die Size-39mil.			
Electrical Characteristics	Symbol	Unit	Spec. limit	Die Sort
Breakdown Voltage @ $I_R=10mA$	V_B	V	30	35
Average Rectified Forward Current	$I_{F(AV)}$	A	1,0	-
DC Forward Voltage @ 25°C, $I_F=1,0A$	V_F	V	0,39	0,37
Maximum Reverse Current @ 25°C, $V_R=33V$ 25°C, $V_R=30V$ 100°C, $V_R=30V$	I_R	MA	- 0,200 30,0	0,200 0,180 25,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	I_{FSM}	A	45	-
Peak Repetitive Reverse Surge Current @2,0µs, f=1kHz., $T_J<150°C$.	I_{RRM}	A	1,0	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	ESD	kV	±8 (contact)	
Voltage Rate of Change	dV/dt	V/µS	10.000	
Operating Junction Temperature	T_J	°C	150	



DIM	ITEM	µm
A _x A _y	Die Size	1000 1000
B _x B _y	Top Metal Size	860 860
D	Thickness	300max.
Scribe line Width		80

Top metal: a) **Al** – for Wire Bonding;
b) **Al-Ni-Ag** – for Soldering.
Backside metal: **Ti-Ni-Ag**.